

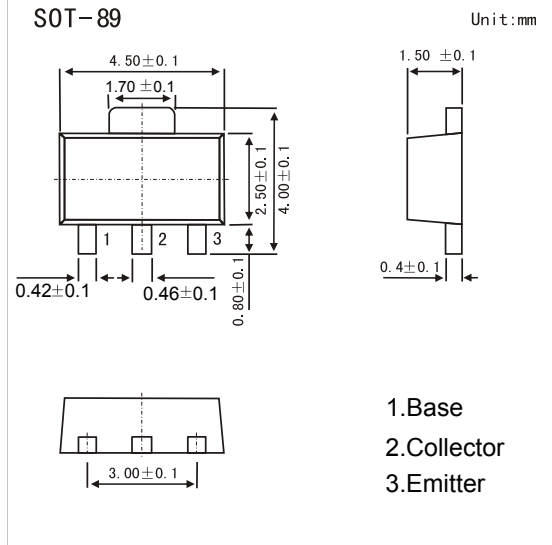
SOT-89 Plastic-Encapsulate Transistors

Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to KTC4375
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-30	V
Collector - Emitter Voltage	V _{CEO}	-30	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-1.5	A
Base Current	I _B	-0.3	
Collector Power Dissipation	P _C	500	mW
		1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
KTA1663	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -1 mA, I _E =0	-30			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B =0	-30			
Emitter - base breakdown voltage	V _{EBO}	I _E = -1 mA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -30V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1.5 A, I _B =-30mA			-2	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-1.5 A, I _B =-30mA			-1.2	
Base - emitter voltage	V _{BE}	V _{CE} = -2V, I _C = -500mA			-1	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -500mA	100		320	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz			50	pF
Transition frequency	f _T	V _{CE} = -2V, I _C = -500mA		120		MHz

Classification of h_{FE}

Type	KTA1663-O	KTA1663-Y
Range	100-200	160-320
Marking	HO	HY

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

